

FORM PTO-1449/A and B (Modified)

APPLICATION NO.: 09/662,471

ATTY. DOCKET NO.: V00077/70162

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

FILING DATE: September 15, 2000

APPLICANT: Svetlana B. Radovanov et al.

GROUP ART UNIT: 2858

EXAMINER: Not Yet Assigned

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## U.S. PATENT DOCUMENTS

Examiner's Initials#	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication or of issue of Cited Document MM-DD-YYYY
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EXAMINER

DATE CONSIDERED

Trang Nguyen

11/15/02

#EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

\*a copy of this reference is not provided as it was previously cited by or submitted to the office in a prior application, Serial No. \_\_\_\_\_, filed \_\_\_\_\_, and relied upon for an earlier filing date under 35 U.S.C. 120 (continuation, continuation-in-part, and divisional applications).

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